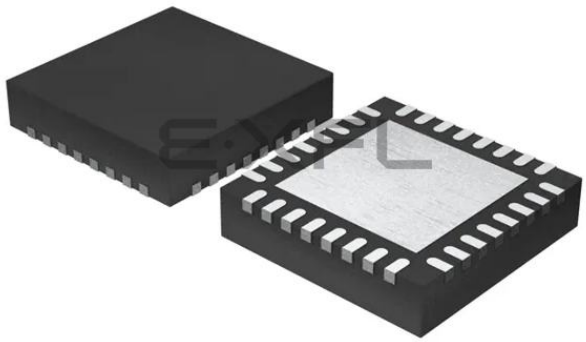

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I²C, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, LVD, POR, PWM, WDT
Number of I/O	28
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 14x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount, Wettable Flank
Package / Case	32-VFQFN Exposed Pad
Supplier Device Package	32-HVQFN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mkl05z32vfm4r

Table of Contents

Field	Description	Values
T	Temperature range (°C)	• V = –40 to 105
PP	Package identifier	• FK = 24 QFN (4 mm x 4 mm) • LC = 32 LQFP (7 mm x 7 mm) • FM = 32 QFN (5 mm x 5 mm) • LF = 48 LQFP (7 mm x 7 mm)
CC	Maximum CPU frequency (MHz)	• 4 = 48 MHz
N	Packaging type	• R = Tape and reel • (Blank) = Trays

2.4 Example

This is an example part number:

MKL05Z8VLC4

3 Terminology and guidelines

3.1 Definition: Operating requirement

An *operating requirement* is a specified value or range of values for a technical characteristic that you must guarantee during operation to avoid incorrect operation and possibly decreasing the useful life of the chip.

3.1.1 Example

This is an example of an operating requirement, which you must meet for the accompanying operating behaviors to be guaranteed:

Symbol	Description	Min.	Max.	Unit
V_{DD}	1.0 V core supply voltage	0.9	1.1	V

3.7 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.
- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.

3.8 Definition: Typical value

A *typical value* is a specified value for a technical characteristic that:

- Lies within the range of values specified by the operating behavior
- Given the typical manufacturing process, is representative of that characteristic during operation when you meet the typical-value conditions or other specified conditions

Typical values are provided as design guidelines and are neither tested nor guaranteed.

3.8.1 Example 1

This is an example of an operating behavior that includes a typical value:

Symbol	Description	Min.	Typ.	Max.	Unit
I_{WP}	Digital I/O weak pullup/pulldown current	10	70	130	µA

3.8.2 Example 2

This is an example of a chart that shows typical values for various voltage and temperature conditions:

4.2 Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level	—	3	—	1

1. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

4.3 ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
V_{HBM}	Electrostatic discharge voltage, human body model	-2000	+2000	V	1
V_{CDM}	Electrostatic discharge voltage, charged-device model	-500	+500	V	2
I_{LAT}	Latch-up current at ambient temperature of 105°C	-100	+100	mA	

1. Determined according to JEDEC Standard JESD22-A114, *Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM)*.
2. Determined according to JEDEC Standard JESD22-C101, *Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components*.

4.4 Voltage and current operating ratings

Symbol	Description	Min.	Max.	Unit
V_{DD}	Digital supply voltage	–0.3	3.8	V
I_{DD}	Digital supply current	—	120	mA
V_{DIO}	Digital pin input voltage (except $\overline{\text{RESET}}$)	–0.3	V_{DD} + 0.3	V
V_{AIO}	Analog pins[1] and $\overline{\text{RESET}}$ pin input voltage	–0.3	V_{DD} + 0.3	V
I_D	Instantaneous maximum current single pin limit (applies to all port pins)	–25	25	mA
V_{DDA}	Analog supply voltage	V_{DD} – 0.3	V_{DD} + 0.3	V

1. Analog pins are defined as pins that do not have an associated general purpose I/O port function.

5 General

Table 1. Voltage and current operating requirements (continued)

Symbol	Description	Min.	Max.	Unit	Notes
I_{ICIO}	I/O pin DC injection current — single pin • $V_{IN} < V_{SS}$-0.3V (Negative current injection) • $V_{IN} > V_{DD}$+0.3V (Positive current injection)	 -3 —	 — +3	mA	1
I_{ICcont}	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents or sum of positive injection currents of 16 contiguous pins • Negative current injection • Positive current injection	 -25 —	 — +25	mA	
V_{RAM}	V_{DD} voltage required to retain RAM	1.2	—	V	

1. All analog pins are internally clamped to V_{SS} and V_{DD} through ESD protection diodes. If V_{IN} is greater than V_{AIO_MIN} (=V_{SS}-0.3V) and V_{IN} is less than V_{AIO_MAX}(=V_{DD}+0.3V) is observed, then there is no need to provide current limiting resistors at the pads. If these limits cannot be observed then a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as $R=(V_{AIO\_MIN}-V_{IN})/|I_{IC}|$. The positive injection current limiting resistor is calcualted as $R=(V_{IN}-V_{AIO\_MAX})/|I_{IC}|$. Select the larger of these two calculated resistances.

5.2.2 LVD and POR operating requirements

Table 2. V_{DD} supply LVD and POR operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR}	Falling V_{DD} POR detect voltage	0.8	1.1	1.5	V	
V_{LVDH}	Falling low-voltage detect threshold — high range (LVDV=01)	2.48	2.56	2.64	V	
	Low-voltage warning thresholds — high range					1
V_{LVW1H}	• Level 1 falling (LVWV=00)	2.62	2.70	2.78	V	
V_{LVW2H}	• Level 2 falling (LVWV=01)	2.72	2.80	2.88	V	
V_{LVW3H}	• Level 3 falling (LVWV=10)	2.82	2.90	2.98	V	
V_{LVW4H}	• Level 4 falling (LVWV=11)	2.92	3.00	3.08	V	
V_{HYSH}	Low-voltage inhibit reset/recover hysteresis — high range	—	±60	—	mV	
V_{LVDL}	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	
	Low-voltage warning thresholds — low range					1
V_{LVW1L}	• Level 1 falling (LVWV=00)	1.74	1.80	1.86	V	
V_{LVW2L}	• Level 2 falling (LVWV=01)	1.84	1.90	1.96	V	
V_{LVW3L}	• Level 3 falling (LVWV=10)	1.94	2.00	2.06	V	
V_{LVW4L}	• Level 4 falling (LVWV=11)	2.04	2.10	2.16	V	
V_{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	—	±40	—	mV	

Table continues on the next page...

Table 2. V_{DD} supply LVD and POR operating requirements (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	
t_{LPO}	Internal low power oscillator period — factory trimmed	900	1000	1100	µs	

1. Rising thresholds are falling threshold + hysteresis voltage

5.2.3 Voltage and current operating behaviors

Table 3. Voltage and current operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V_{OH}	Output high voltage — Normal drive pad				1
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH} = -5 mA	V_{DD} – 0.5	—	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OH} = -1.5 mA	V_{DD} – 0.5	—	V	
V_{OH}	Output high voltage — High drive pad				1
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH} = -18 mA	V_{DD} – 0.5	—	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OH} = -6 mA	V_{DD} – 0.5	—	V	
I_{OHT}	Output high current total for all ports	—	100	mA	
V_{OL}	Output low voltage — Normal drive pad				1
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 5 mA	—	0.5	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OL} = 1.5 mA	—	0.5	V	
V_{OL}	Output low voltage — High drive pad				1
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 18 mA	—	0.5	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OL} = 6 mA	—	0.5	V	
I_{OLT}	Output low current total for all ports	—	100	mA	
I_{IN}	Input leakage current (per pin) for full temperature range	—	1	µA	2
I_{IN}	Input leakage current (per pin) at 25 °C	—	0.025	µA	2
I_{IN}	Input leakage current (total all pins) for full temperature range	—	41	µA	2
I_{OZ}	Hi-Z (off-state) leakage current (per pin)	—	1	µA	
R_{PU}	Internal pullup resistors	20	50	kΩ	3

1. PTA12, PTA13, PTB0 and PTB1 I/O have both high drive and normal drive capability selected by the associated PTx_PCRn[DSE] control bit. All other GPIOs are normal drive only.
2. Measured at V_{DD} = 3.6 V
3. Measured at V_{DD} supply voltage = V_{DD} min and Vinput = V_{SS}

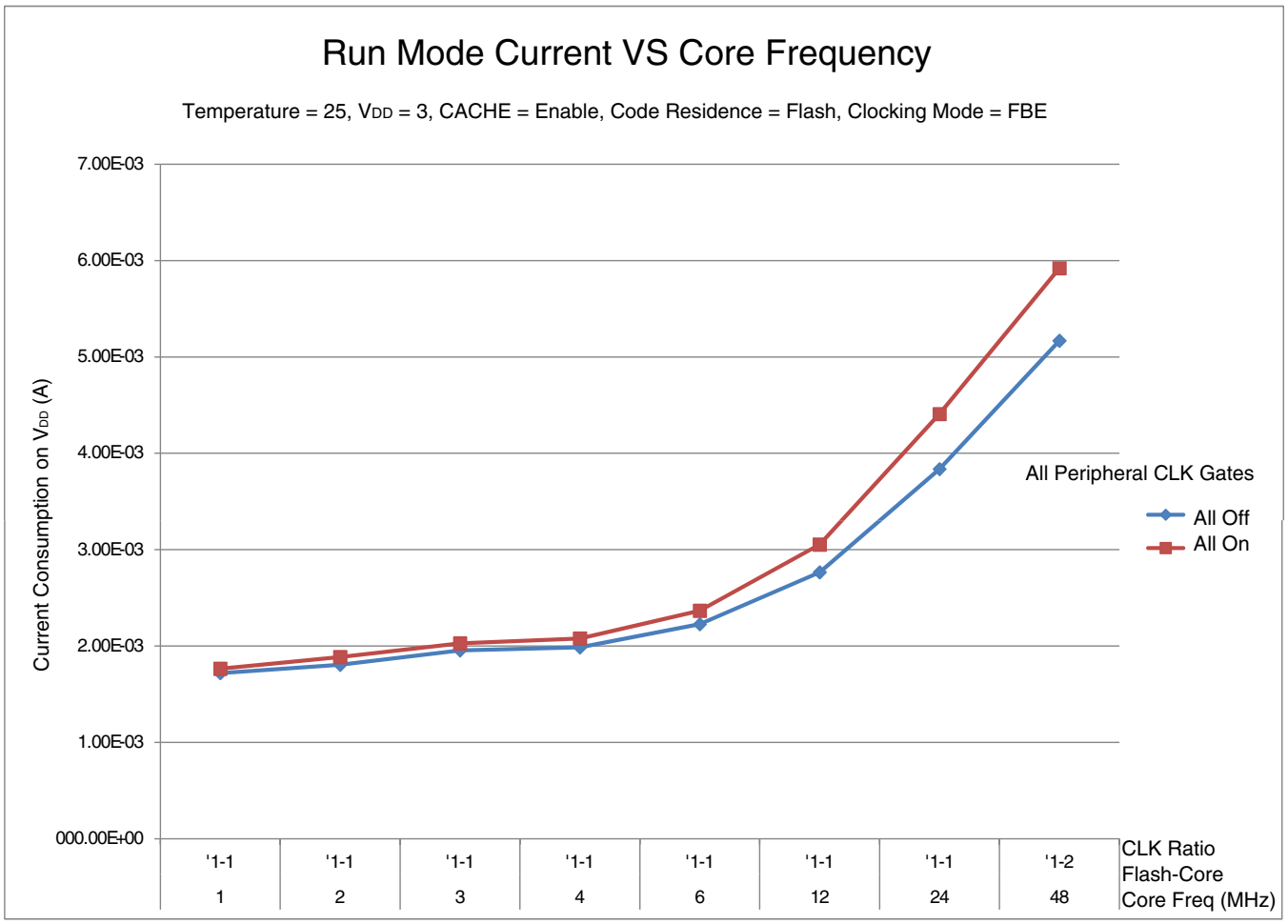


Figure 2. Run mode supply current vs. core frequency

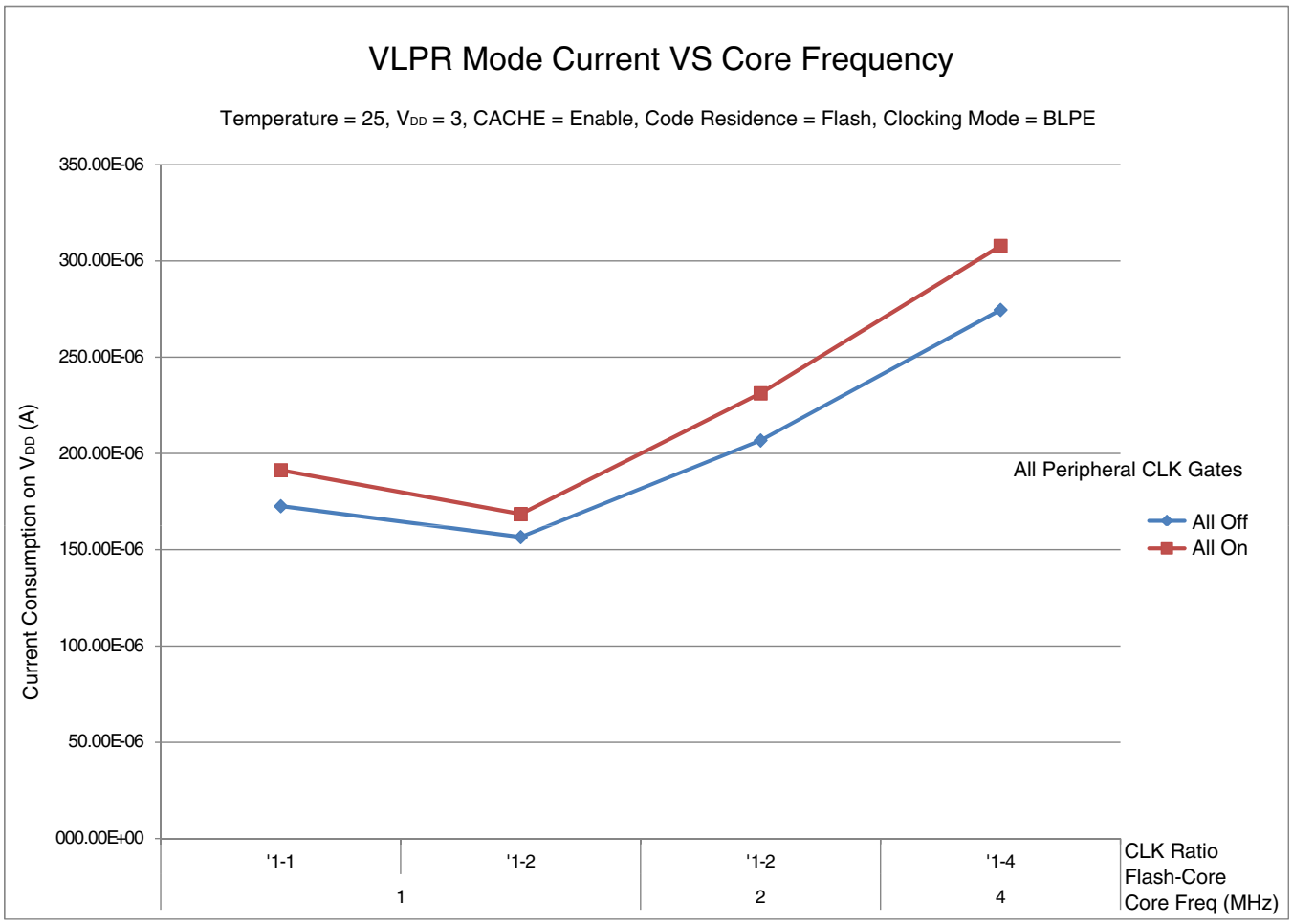


Figure 3. VLPR mode current vs. core frequency

5.2.6 Designing with radiated emissions in mind

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions:

1. Go to www.freescale.com.
2. Perform a keyword search for "EMC design."

5.2.7 Capacitance attributes

Table 7. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C_{IN_A}	Input capacitance: analog pins	—	7	pF
C_{IN_D}	Input capacitance: digital pins	—	7	pF

1. The greater synchronous and asynchronous timing must be met.
2. This is the shrtest pulse that is guaranteed to be recognized.
3. 75 pF load

5.4 Thermal specifications

5.4.1 Thermal operating requirements

Table 8. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit
T_J	Die junction temperature	–40	125	°C
T_A	Ambient temperature	–40	105	°C

5.4.2 Thermal attributes

Table 9. Thermal attributes

Board type	Symbol	Description	48 LQFP	32 LQFP	32 QFN	24 QFN	Unit	Notes
Single-layer (1S)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	82	88	97	110	°C/W	1
Four-layer (2s2p)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	58	59	34	42	°C/W	
Single-layer (1S)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	70	74	81	92	°C/W	
Four-layer (2s2p)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	52	52	28	36	°C/W	
—	$R_{\theta JB}$	Thermal resistance, junction to board	36	35	13	18	°C/W	2
—	$R_{\theta JC}$	Thermal resistance, junction to case	27	26	2.3	3.7	°C/W	3
—	Ψ_{JT}	Thermal characterization parameter, junction to package top outside center (natural convection)	8	8	8	10	°C/W	4

1. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)*, or EIA/JEDEC Standard JESD51-6, *Integrated Circuit Thermal Test Method Environmental Conditions—Forced Convection (Moving Air)*.
2. Determined according to JEDEC Standard JESD51-8, *Integrated Circuit Thermal Test Method Environmental Conditions—Junction-to-Board*.

3. Proper PC board layout procedures must be followed to achieve specifications.
4. Crystal startup time is defined as the time between the oscillator being enabled and the OSCINIT bit in the MCG_S register being set.

NOTE

The 32 kHz oscillator works in low power mode by default and cannot be moved into high power/gain mode.

6.4 Memories and memory interfaces

6.4.1 Flash electrical specifications

This section describes the electrical characteristics of the flash memory module.

6.4.1.1 Flash timing specifications — program and erase

The following specifications represent the amount of time the internal charge pumps are active and do not include command overhead.

Table 14. NVM program/erase timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{hvpgm4}	Longword Program high-voltage time	—	7.5	18	µs	
$t_{hversscr}$	Sector Erase high-voltage time	—	13	113	ms	1

1. Maximum time based on expectations at cycling end-of-life.

6.4.1.2 Flash timing specifications — commands

Table 15. Flash command timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{rd1sec1k}$	Read 1s Section execution time (flash sector)	—	—	60	µs	1
t_{pgmchk}	Program Check execution time	—	—	45	µs	1
t_{rdrsrc}	Read Resource execution time	—	—	30	µs	1
t_{pgm4}	Program Longword execution time	—	65	145	µs	
t_{ersscr}	Erase Flash Sector execution time	—	14	114	ms	2
t_{rd1all}	Read 1s All Blocks execution time	—	—	0.5	ms	
t_{rdonce}	Read Once execution time	—	—	25	µs	1
$t_{pgmonce}$	Program Once execution time	—	65	—	µs	
t_{ersall}	Erase All Blocks execution time	—	55	465	ms	2
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	30	µs	1

1. Assumes 25 MHz flash clock frequency.

2. Maximum times for erase parameters based on expectations at cycling end-of-life.

6.4.1.3 Flash high voltage current behaviors

Table 16. Flash high voltage current behaviors

Symbol	Description	Min.	Typ.	Max.	Unit
I_{DD_PGM}	Average current adder during high voltage flash programming operation	—	2.5	6.0	mA
I_{DD_ERS}	Average current adder during high voltage flash erase operation	—	1.5	4.0	mA

6.4.1.4 Reliability specifications

Table 17. NVM reliability specifications

Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
Program Flash						
$t_{nvmretp10k}$	Data retention after up to 10 K cycles	5	50	—	years	
$t_{nvmretp1k}$	Data retention after up to 1 K cycles	20	100	—	years	
$n_{nvmcycp}$	Cycling endurance	10 K	50 K	—	cycles	2

1. Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25°C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.
2. Cycling endurance represents number of program/erase cycles at -40°C ≤ T_j ≤ 125°C.

6.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

6.6 Analog

6.6.1 ADC electrical specifications

All ADC channels meet the 12-bit single-ended accuracy specifications.

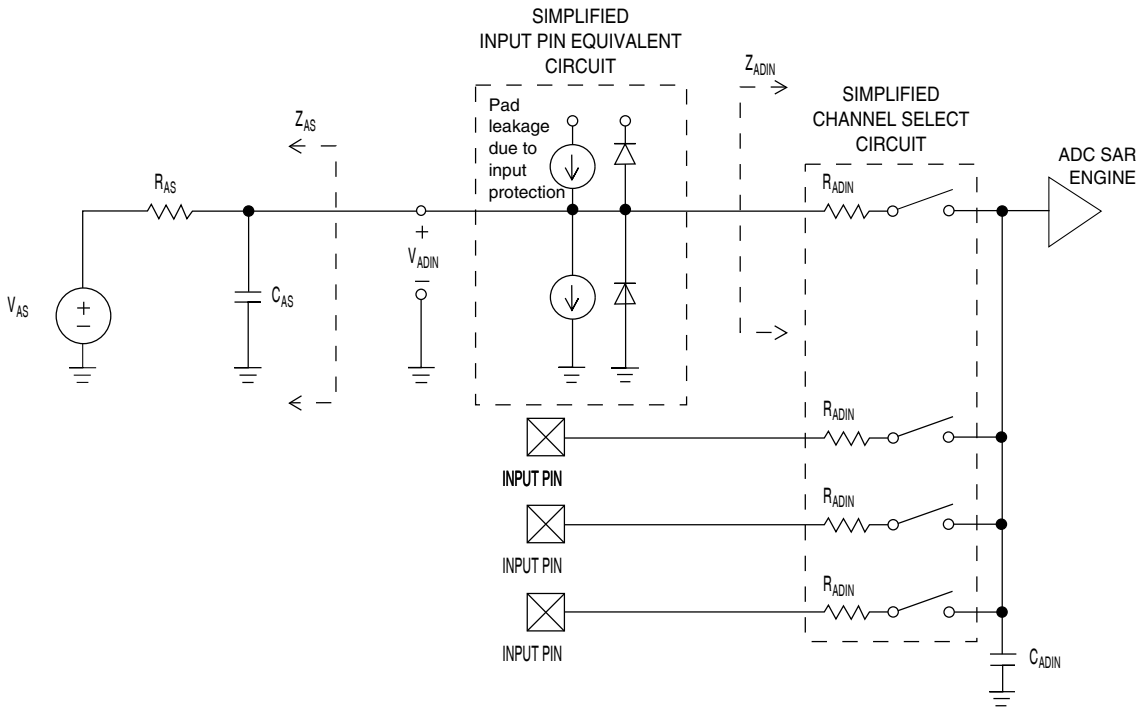


Figure 6. ADC input impedance equivalency diagram

6.6.1.2 12-bit ADC electrical characteristics

Table 19. 12-bit ADC characteristics (V_{REFH} = V_{DDA}, V_{REFL} = V_{SSA})

Symbol	Description	Conditions[1]	Min.	Typ.[2]	Max.	Unit	Notes
I_{DDA_ADC}	Supply current		0.215	—	1.7	mA	3
f_{ADACK}	ADC asynchronous clock source	• ADLPC = 1, ADHSC = 0 • ADLPC = 1, ADHSC = 1 • ADLPC = 0, ADHSC = 0 • ADLPC = 0, ADHSC = 1	1.2 2.4 3.0 4.4	2.4 4.0 5.2 6.2	3.9 6.1 7.3 9.5	MHz MHz MHz MHz	t_{ADACK} = 1/ f_{ADACK}
	Sample Time	See Reference Manual chapter for sample times					
TUE	Total unadjusted error	• 12-bit modes • <12-bit modes	— —	±4 ±1.4	±6.8 ±2.1	LSB[4]	5
DNL	Differential non-linearity	• 12-bit modes • <12-bit modes	— —	±0.7 ±0.2	-1.1 to +1.9 -0.3 to 0.5	LSB[4]	5
INL	Integral non-linearity	• 12-bit modes • <12-bit modes	— —	±1.0 ±0.5	-2.7 to +1.9 -0.7 to +0.5	LSB[4]	5
E_{FS}	Full-scale error	• 12-bit modes • <12-bit modes	— —	-4 -1.4	-5.4 -1.8	LSB[4]	V_{ADIN} = V_{DDA} 5

Table continues on the next page...

6.6.2 CMP and 6-bit DAC electrical specifications

Table 20. Comparator and 6-bit DAC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V_{DD}	Supply voltage	1.71	—	3.6	V
I_{DDHS}	Supply current, high-speed mode (EN = 1, PMODE = 1)	—	—	200	µA
I_{DDLS}	Supply current, low-speed mode (EN = 1, PMODE = 0)	—	—	20	µA
V_{AIN}	Analog input voltage	V_{SS}	—	V_{DD}	V
V_{AIO}	Analog input offset voltage	—	—	20	mV
V_H	Analog comparator hysteresis[1]				
	• CR0[HYSTCTR] = 00	—	5	—	mV
	• CR0[HYSTCTR] = 01	—	10	—	mV
	• CR0[HYSTCTR] = 10	—	20	—	mV
	• CR0[HYSTCTR] = 11	—	30	—	mV
V_{CMPOh}	Output high	$V_{DD} – 0.5$	—	—	V
V_{CMPOl}	Output low	—	—	0.5	V
t_{DHS}	Propagation delay, high-speed mode (EN = 1, PMODE = 1)	20	50	200	ns
t_{DLS}	Propagation delay, low-speed mode (EN = 1, PMODE = 0)	80	250	600	ns
	Analog comparator initialization delay[2]	—	—	40	µs
I_{DAC6b}	6-bit DAC current adder (enabled)	—	7	—	µA
INL	6-bit DAC integral non-linearity	–0.5	—	0.5	LSB[3]
DNL	6-bit DAC differential non-linearity	–0.3	—	0.3	LSB

1. Typical hysteresis is measured with input voltage range limited to 0.7 to $V_{DD} – 0.7$ V.
2. Comparator initialization delay is defined as the time between software writes to change control inputs (writes to DACEN, VRSEL, PSEL, MSEL, VOSEL) and the comparator output settling to a stable level.
3. 1 LSB = $V_{reference}/64$

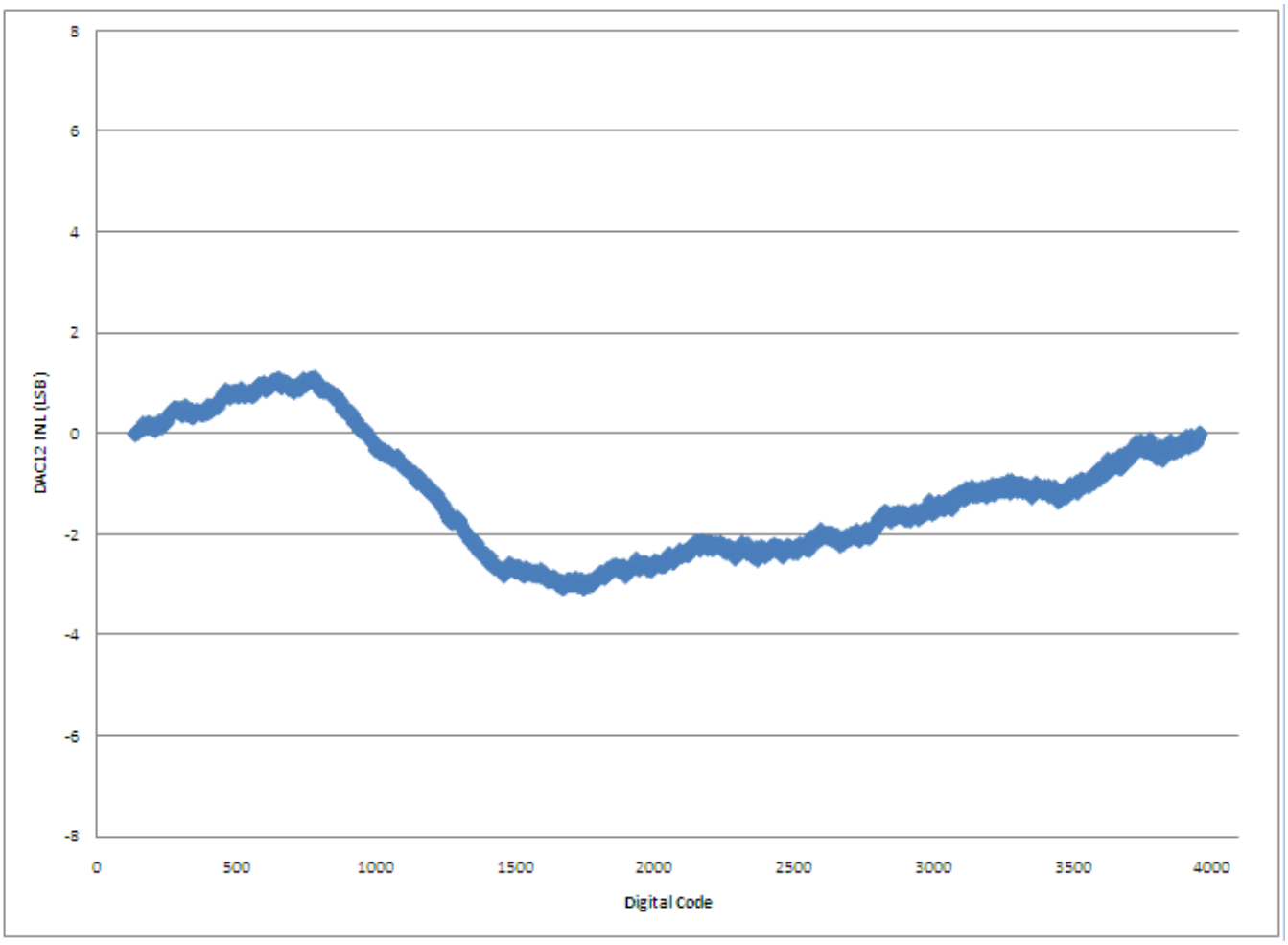
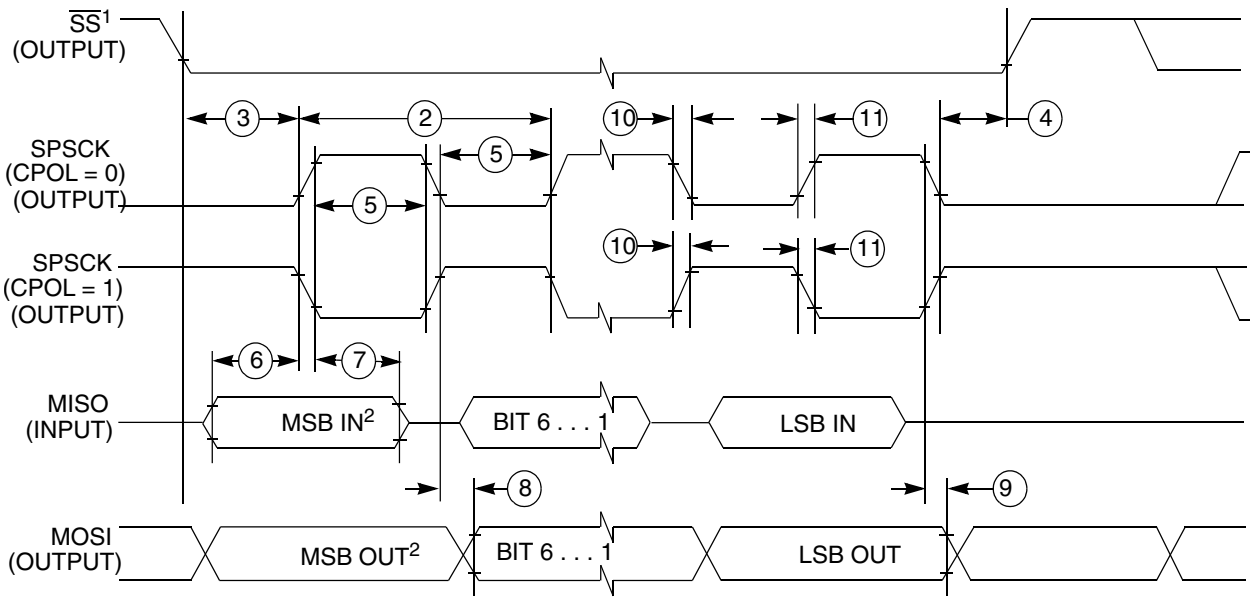
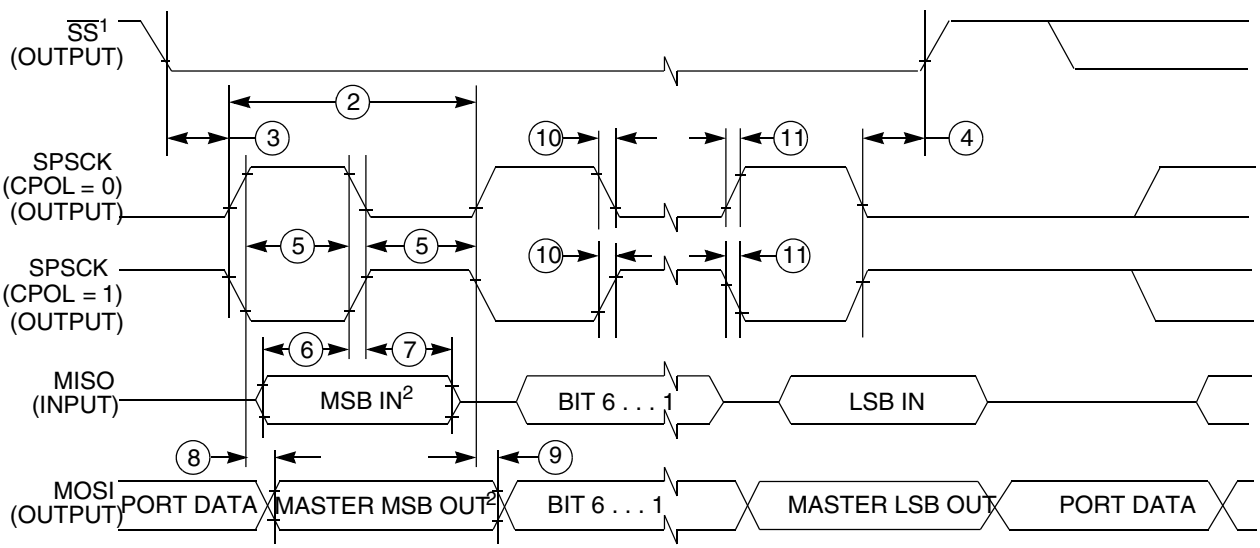


Figure 10. Typical INL error vs. digital code



1. If configured as an output.
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 12. SPI master mode timing (CPHA = 0)



1.If configured as output

2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 13. SPI master mode timing (CPHA = 1)

Table 25. SPI slave mode timing on slew rate disabled pads

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f_{op}	Frequency of operation	0	$f_{periph}/4$	Hz	1
2	t_{SPSCK}	SPSCK period	4 x t_{periph}	—	ns	2
3	t_{Lead}	Enable lead time	1	—	t_{periph}	—
4	t_{Lag}	Enable lag time	1	—	t_{periph}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	t_{periph} - 30	—	ns	—

Table continues on the next page...

Table 25. SPI slave mode timing on slew rate disabled pads (continued)

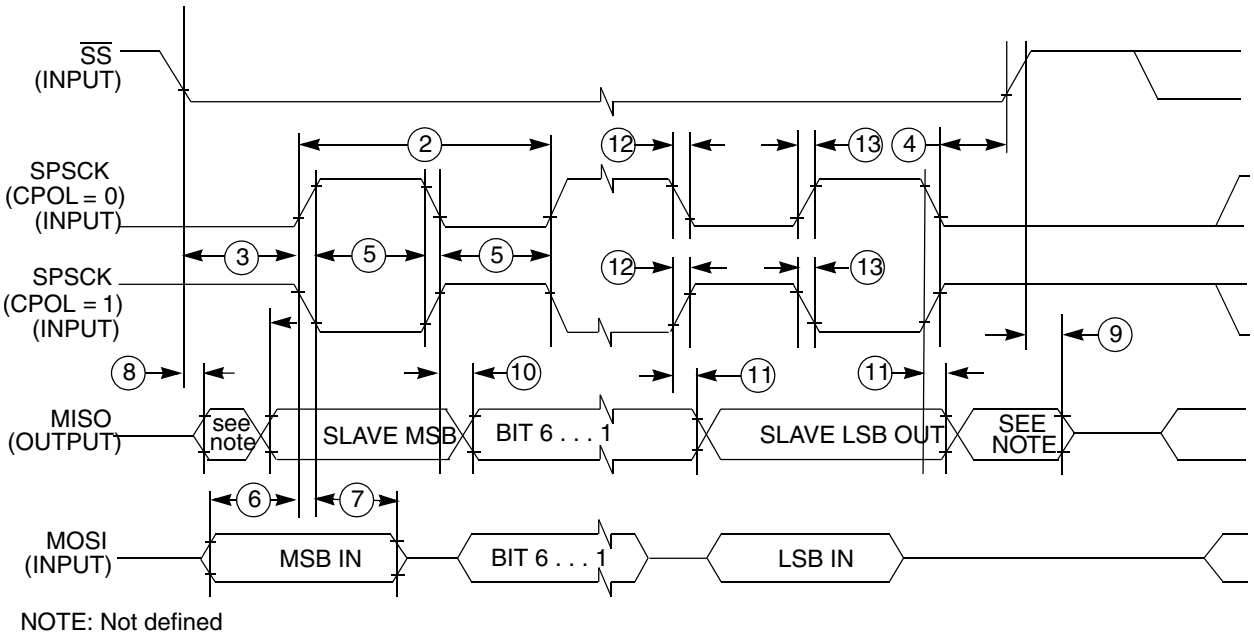
Num.	Symbol	Description	Min.	Max.	Unit	Note
6	t_{SU}	Data setup time (inputs)	2	—	ns	—
7	t_{HI}	Data hold time (inputs)	7	—	ns	—
8	t_a	Slave access time	—	t_{periph}	ns	3
9	t_{dis}	Slave MISO disable time	—	t_{periph}	ns	4
10	t_v	Data valid (after SPSCK edge)	—	22	ns	—
11	t_{HO}	Data hold time (outputs)	0	—	ns	—
12	t_{RI}	Rise time input	—	t_{periph} - 25	ns	—
	t_{FI}	Fall time input				
13	t_{RO}	Rise time output	—	25	ns	—
	t_{FO}	Fall time output				

1. For SPI0 f_{periph} is the bus clock (f_{BUS}).
2. $t_{periph} = 1/f_{periph}$
3. Time to data active from high-impedance state
4. Hold time to high-impedance state

Table 26. SPI slave mode timing on slew rate enabled pads

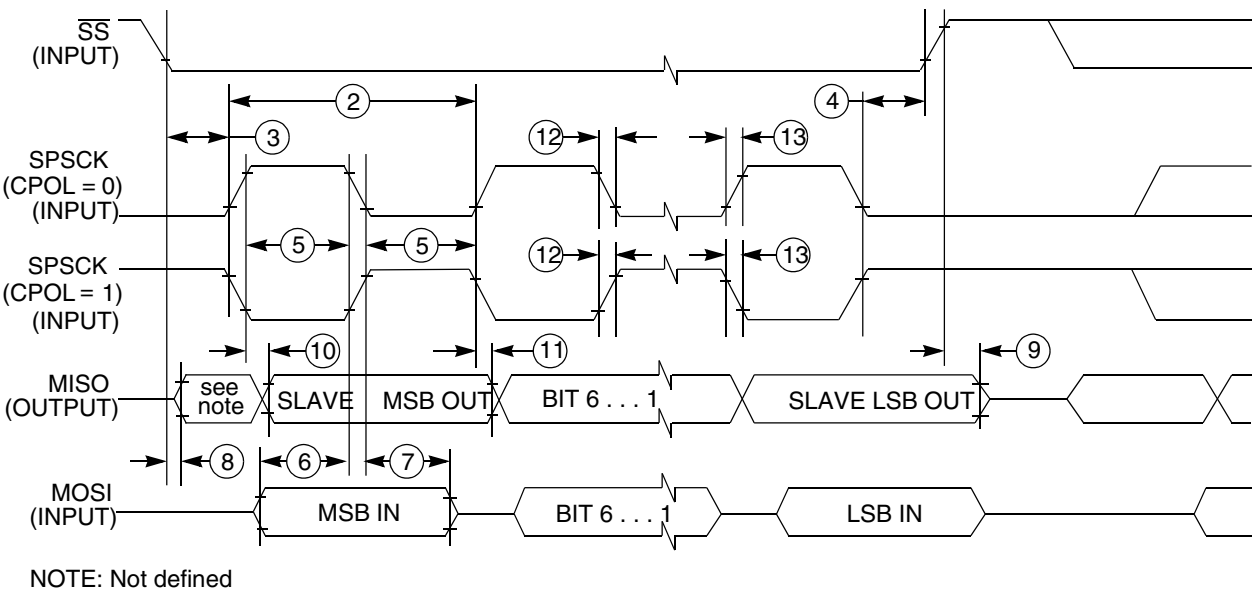
Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f_{op}	Frequency of operation	0	$f_{periph}/4$	Hz	1
2	t_{SPSCK}	SPSCK period	4 x t_{periph}	—	ns	2
3	t_{Lead}	Enable lead time	1	—	t_{periph}	—
4	t_{Lag}	Enable lag time	1	—	t_{periph}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	t_{periph} - 30	—	ns	—
6	t_{SU}	Data setup time (inputs)	2	—	ns	—
7	t_{HI}	Data hold time (inputs)	7	—	ns	—
8	t_a	Slave access time	—	t_{periph}	ns	3
9	t_{dis}	Slave MISO disable time	—	t_{periph}	ns	4
10	t_v	Data valid (after SPSCK edge)	—	122	ns	—
11	t_{HO}	Data hold time (outputs)	0	—	ns	—
12	t_{RI}	Rise time input	—	t_{periph} - 25	ns	—
	t_{FI}	Fall time input				
13	t_{RO}	Rise time output	—	36	ns	—
	t_{FO}	Fall time output				

1. For SPI0 f_{periph} is the bus clock (f_{BUS}).
2. $t_{periph} = 1/f_{periph}$
3. Time to data active from high-impedance state
4. Hold time to high-impedance state



NOTE: Not defined

Figure 14. SPI slave mode timing (CPHA = 0)



NOTE: Not defined

Figure 15. SPI slave mode timing (CPHA = 1)

6.8.2 I²C

See General switching specifications.

6.8.3 UART

See General switching specifications.

8.2 KL05 Pinouts

The following figures show the pinout diagrams for the devices supported by this document. Many signals may be multiplexed onto a single pin. To determine what signals can be used on which pin, see the previous section.

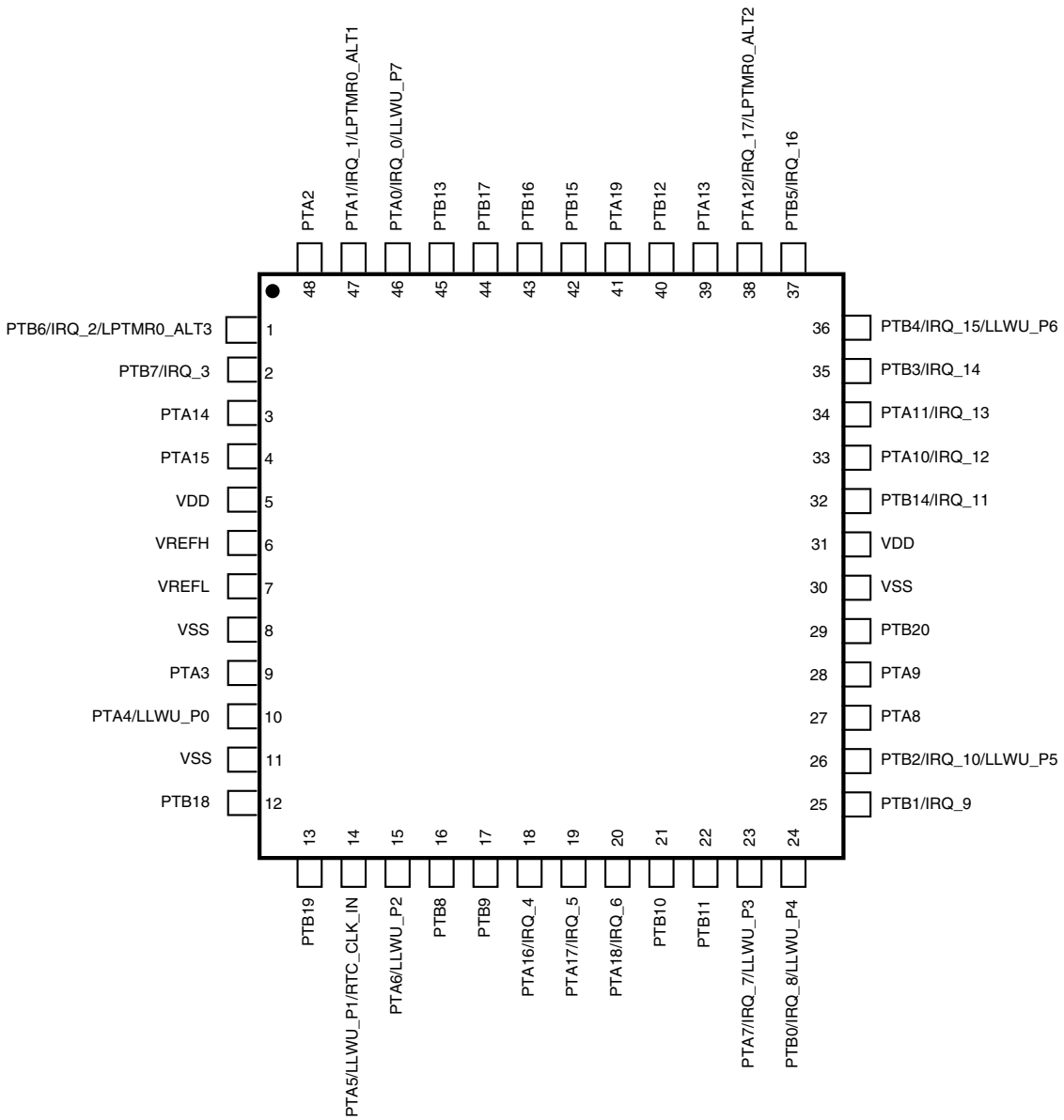


Figure 16. KL05 48-pin LQFP pinout diagram

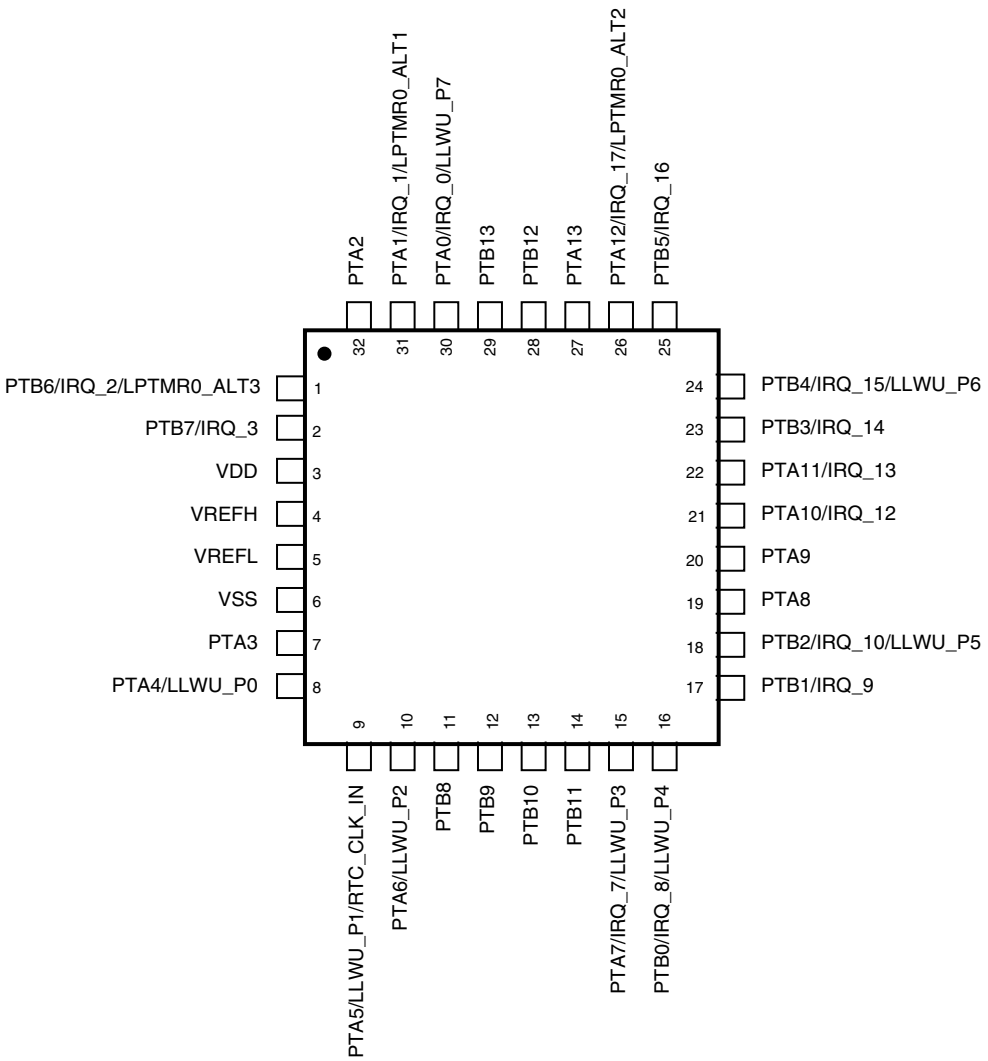


Figure 17. KL05 32-pin LQFP pinout diagram

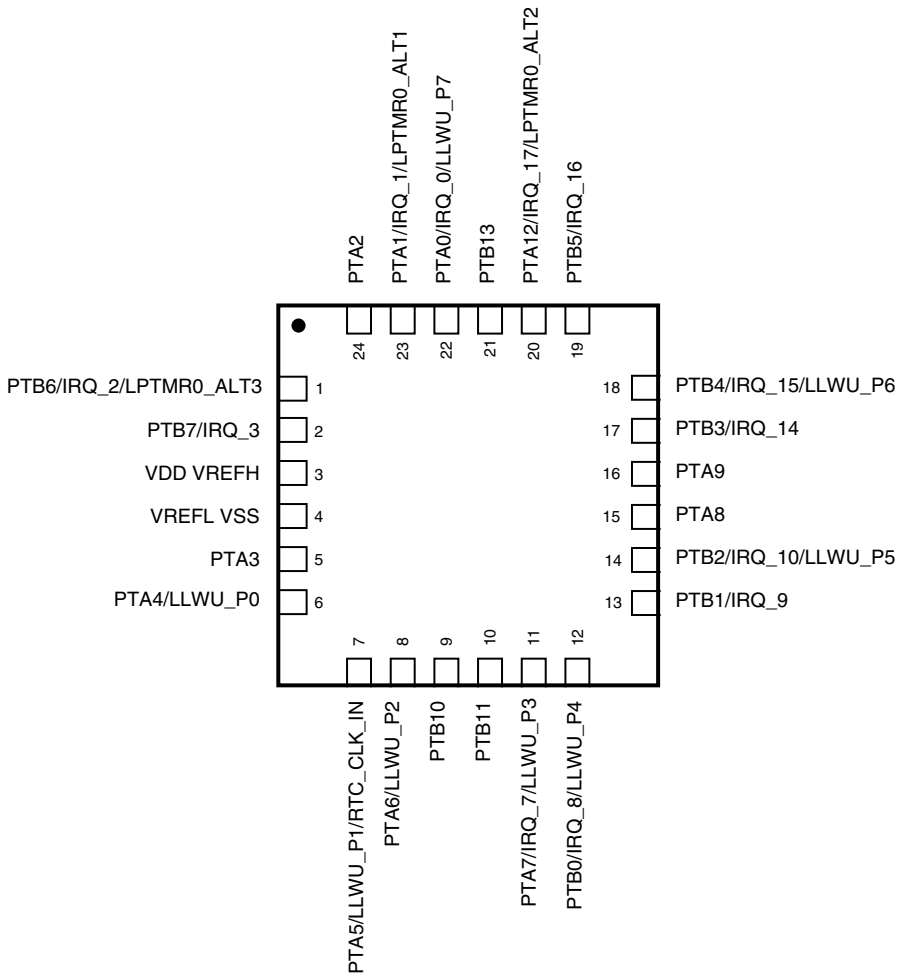


Figure 19. KL05 24-pin QFN pinout diagram

9 Revision History

The following table provides a revision history for this document.

Table 28. Revision History

Rev. No.	Date	Substantial Changes
1	7/2012	Initial NDA release.
2	9/2012	Initial public release.
3	11/2012	Completed all the TBDs.